Preparation and Study of Heterojunctions Based on Chalcogenide Glassy Semiconductors

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Four types of heterojunctions were prepared: SnO_2-$As_2(Se_{0.9}Te_{0.1})_3$, SnO_2-$(As_{0.67}Sb_{0.33})_2Se_3$, n-GaAs-$As_2Se_3$ and n-GaAs-As_2S_3. For all samples I-V characteristics and photosensitivity spectra were obtained. These heterostructures can be used for manufacturing rectifying devices and photoreceivers.

Key words: Heterostructure; Chalcogenide Glassy Semiconductor; Spectra of Photosensitivity.